‘DOCK/
CHEMICALS
SEMICONDUCTORS DECISION

$C_6H_{16}O_3Si$

Liquid silicon-precursor for CVD applications

´HTEOS - TRIETHOXYSILANE

PRODUCT DATASHEET

´MO-CVD

BP: 134-135 °C/273,2-275 °F/1013 hPa

´HTEOS - TRIETHOXYSILANE

´MO-CVD

IDENTIFICATION

CAS-No:	998-30-1
EINECS/ELINCS-No:	213-650-7
Other name:	none

PHYSICAL PROPERTIES

Vapor pressure:	27 hPa at 20 °C
Density:	0.89 g/cm³ at 25 °C
Molweight:	164.27 g/mol
Melting point:	-170 °C / -274 °F
Boiling point (1013 mbar):	134-135 °C / 273.2-275 °F

CHEMICAL PROPERTIES

Stability:	Stable under recommended storage conditions.
State of matter:	Liquid

SAFETY & TRANSPORT

Toxicity:	toxic by inhalation
Explosion limit Vol%:	n.a.
Auto ignition temp. °C:	n.a.
ADR/RID	
ADR/RID-class:	6.1 (3.8), PG I
UN-no:	3489
IMDG	
IMDG -class:	6.1 (3.8), PG I
UN-no:	3489
ICAO/IATA	
ICAO/IATA-class:	6.1 (3.8), PG I
UN-no:	3489 - AIRFREIGHT FORBIDDEN

For further details please refer to Safety Data Sheet (SDS)

PACKAGING & STANDARD FILLING VOLUMES

HTEOS.100.DOCK/10.150	100g / 150ccm cyl.
HTEOS.300.DOCK/10.400	300g / 400ccm cyl.
HTEOS.450.DOCK/10.600	450g / 600ccm cyl.
HTEOS.800.DOCK/10.1000	800g / 1000ccm cyl.

QUALITY STANDARDS

PG **Pure Grade**

VAPOR PRESSURE CURVE

n.a.

APPLICATION

Si precursor for SiO_2 deposition

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PRODUCT DATASHEET

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